EB52F3A15N-27.000M

Lead Integrity

Solderability

Vibration

Mechanical Shock

Resistance to Solvents

Temperature Cycling

Resistance to Soldering Heat



EB52F3 A 15 N -27.000M

Series 3.3Vdc 14-Pin DIP LVCMOS TCXO

Operating Temperature Range

0°C to +50°C

Frequency Stability ±1.5ppm Maximum

MIL-STD-883, Method 2004

MIL-STD-202, Method 210

MIL-STD-202, Method 215

MIL-STD-883, Method 2003

MIL-STD-883, Method 1010

MIL-STD-202, Method 213 Condition C

MIL-STD-883, Method 2007 Condition A

	14	27.00011
_	-	

Nominal Frequency
27.000MHz

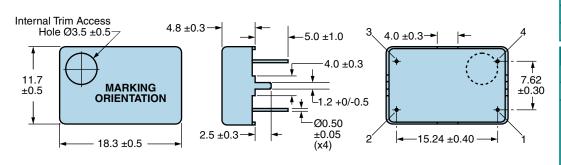
- Control Voltage None (No Connect on Pin 1)

ELECTRICAL SPECIFICATIONS				
Nominal Frequency	27.000MHz			
Frequency Stability	±1.5ppm Maximum (Inclusive of Operating Temperature Range)			
Frequency Stability vs. Input Voltage	±0.3ppm Maximum (±5%)			
Aging at 25°C	±1ppm/Year Maximum			
Frequency Stability vs. Load	±0.2ppm Maximum (±2pF)			
Operating Temperature Range	0°C to +50°C			
Supply Voltage	3.3Vdc ±5%			
Input Current	20mA Maximum			
Output Voltage Logic High (Voh)	90% of Vdd Minimum			
Output Voltage Logic Low (Vol)	10% of Vdd Maximum			
Rise/Fall Time	10nSec Maximum (Measured at 20% to 80% of waveform)			
Duty Cycle	50% ±10% (Measured at 50% of waveform)			
Load Drive Capability	15pF Maximum			
Output Logic Type	CMOS			
Control Voltage	None (No Connect on Pin 1)			
Internal Trim	±3ppm Minimum (Top of Can)			
Modulation Bandwidth	10kHz Minimum (Measured at -3dB with a Control Voltage of 1.65Vdc)			
Input Impedance	10kOhms Typical			
Phase Noise	-70dBc at 10Hz Offset, -100dBc at 100Hz Offset, -130dBc at 1kHz Offset, -140dBc at 10kHz Offset, - 145dBc at 100kHz Offset			
Storage Temperature Range	-40°C to +85°C			
ENVIRONMENTAL & MEC	HANICAL SPECIFICATIONS			
Fine Leak Test	MIL-STD-883, Method 1014 Condition A (Internal Crystal Only)			
Gross Leak Test	MIL-STD-883, Method 1014 Condition C (Internal Crystal Only)			



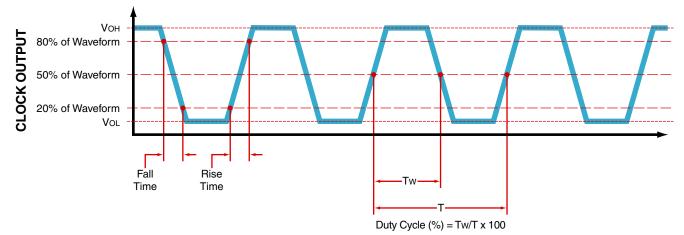
EB52F3A15N-27.000M

MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	No Connect
2	Case/Ground
3	Output
4	Supply Voltage
LINE	MARKING
4	
1	ECLIPTEK
1 2	27.000M

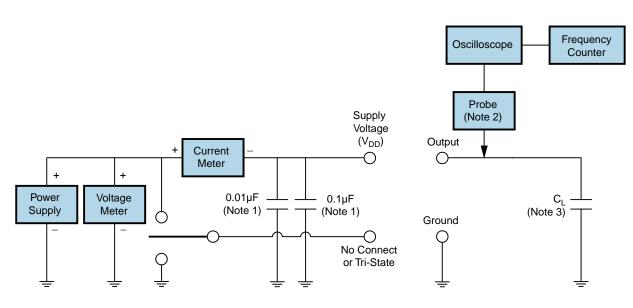
OUTPUT WAVEFORM



EB52F3A15N-27.000M



Test Circuit for CMOS Output



Note 1: An external 0.1µF low frequency tantalum bypass capacitor in parallel with a 0.01µF high frequency ceramic bypass capacitor close to the package ground and V_{DD} pin is required.

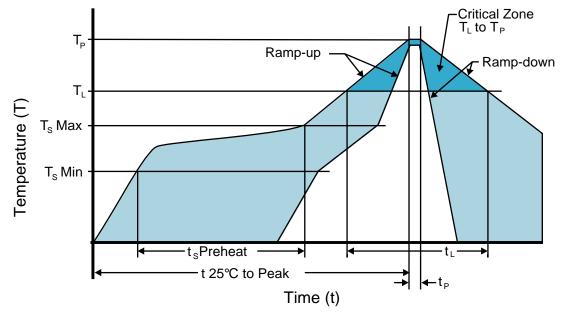
Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value \dot{C}_1 includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods

EB52F3A15N-27.000M



Low Temperature Solder Bath (Wave Solder)

•
5°C/second Maximum
N/A
150°C
N/A
30 - 60 Seconds
5°C/second Maximum
150°C
200 Seconds Maximum
245°C Maximum
245°C Maximum 1 Time / 235°C Maximum 2 Times
5 seconds Maximum 1 Time / 15 seconds Maximum 2 Times
5°C/second Maximum
N/A
Level 1

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum.

Low Temperature Solder Bath (Wave Solder) Note 1

Device is non-hermetic; Post reflow aqueous wash is not recommended

Low Temperature Solder Bath (Wave Solder) Note 2

Temperatures shown are applied to back of PCB board and device leads only.